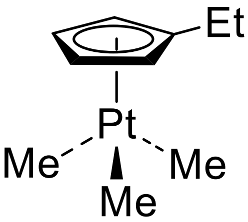
Catalog # T283162 (Trimethyl)ethylcyclopentadienylplatinum(IV)



Thermal behaviour

1. Vapor pressure of 0.1 torr at 39 °C [1]
2. Light sensitive

Technical Notes

1. Organometallic precursor for chemical vapour deposition (CVD) of Pt films [1-3]

Film	Technique	Reactants	Pressure	Temperature	Growth Rate	Substrate	Ref.
Pt	CVD	O_2 (Sol. in THF)	0.7-3 torr	300-450 °C	~20-30 Å/min	Si(100), SiO_2	[1]
Pt	CVD	O_2		340 °C			[2]
Pt	Photo-assisted CVD	H_2	40 Torr				[3]

References:

1. *Chem. Vap. Deposition*, **2003**, *9*, 321.
2. *Jpn. J. Appl. Phys.*, **2004**, *43*, L624.
3. *J. Vac. Sci. Technol. A*, **2007**, *25*, 104.